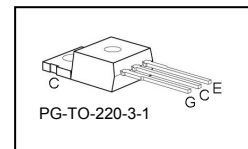
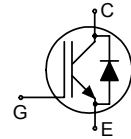


HighSpeed 2-Technology with soft, fast recovery anti-parallel EmCon HE diode

- **Designed for:**
 - SMPS
 - Lamp Ballast
 - ZVS-Converter
 - optimised for soft-switching / resonant topologies
- **2nd generation HighSpeed-Technology for 1200V applications offers:**
 - loss reduction in resonant circuits
 - temperature stable behavior
 - parallel switching capability
 - tight parameter distribution
 - E_{off} optimized for $I_C = 1A$
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC² for target applications
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	V_{CE}	I_C	E_{off}	T_j	Marking	Package
IKP01N120H2	1200V	1A	0.09mJ	150°C	K01H1202	PG-TO-220-3-1

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
Triangular collector current	I_C	3.2	A
$T_C = 25^\circ\text{C}$, $f = 140\text{kHz}$		1.3	
$T_C = 100^\circ\text{C}$, $f = 140\text{kHz}$		3.5	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	3.5	
Turn off safe operating area	-	3.5	
$V_{CE} \leq 1200\text{V}$, $T_j \leq 150^\circ\text{C}$			
Diode forward current	I_F	3.2	
$T_C = 25^\circ\text{C}$		1.3	
$T_C = 100^\circ\text{C}$			
Gate-emitter voltage	V_{GE}	± 20	V
Power dissipation	P_{tot}	28	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j , T_{stg}	-40...+150	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

² J-STD-020 and JEDEC-022

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		4.5	K/W
Diode thermal resistance, Junction - case	R_{thJCD}		11	
Thermal resistance, junction – ambient	R_{thJA}	PG-TO-220-3-1	62	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=300\mu A$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=1A$ $T_j=25^{\circ}C$ $T_j=150^{\circ}C$ $V_{GE} = 10V, I_C=1A,$ $T_j=25^{\circ}C$	- - -	2.2 2.5 2.4	2.8 - -	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=30\mu A, V_{CE}=V_{GE}$	2.1	3	3.9	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^{\circ}C$ $T_j=150^{\circ}C$	- -	- -	20 80	
Diode forward voltage	V_F	$V_{GE} = 0, I_F=0.5A$ $T_j=25^{\circ}C$ $T_j=150^{\circ}C$	- -	2.0 1.75	2.5 -	V
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	40	
Transconductance	g_{fs}	$V_{CE}=20V, I_C=1A$	-	0.75	-	S
Dynamic Characteristic						
Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$	-	91.6	-	pF
Output capacitance	C_{oss}		-	9.8	-	
Reverse transfer capacitance	C_{rss}		-	3.4	-	
Gate charge	Q_{Gate}	$V_{CC}=960V, I_C=1A$ $V_{GE}=15V$	-	8.6	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	7	-	nH

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit	
			min.	Typ.	max.		
IGBT Characteristic							
Turn-on delay time	$t_{d(on)}$	$T_j=25^{\circ}\text{C}$, $V_{CC}=800\text{V}$, $I_C=1\text{A}$, $V_{GE}=15\text{V}/0\text{V}$,	-	13	-	ns	
Rise time	t_r		$V_{CC}=800\text{V}$,	-	6.3		-
Turn-off delay time	$t_{d(off)}$		$I_C=1\text{A}$,	-	370		-
Fall time	t_f		$V_{GE}=15\text{V}/0\text{V}$,	-	28		-
Turn-on energy	E_{on}	$R_G=241\Omega$, $L_{\sigma}^{(2)}=180\text{nH}$, $C_{\sigma}^{(2)}=40\text{pF}$	-	0.08	-	mJ	
Turn-off energy	E_{off}		-	0.06	-		
Total switching energy	E_{ts}		Energy losses include “tail” and diode ³⁾ reverse recovery.	-	0.14		-

Anti-Parallel Diode Characteristic

Diode reverse recovery time	t_{rr}	$T_j=25^\circ\text{C}$, $V_R=800\text{V}$, $I_F=1\text{A}$, $R_G=241\Omega$	-	83	-	ns
Diode reverse recovery charge	Q_{rr}		-	89	-	μC
Diode peak reverse recovery current	I_{rrm}		-	2.5	-	A
Diode current slope	di_F/dt		-	289	-	A/ μs
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	178	-	

Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=150^{\circ}\text{C}$	-	12	-	ns
Rise time	t_r	$V_{CC}=800\text{V}$,	-	8.9	-	
Turn-off delay time	$t_{d(off)}$	$I_C=1\text{A}$,	-	450	-	
Fall time	t_f	$V_{GE}=15\text{V}/0\text{V}$,	-	43	-	
Turn-on energy	E_{on}	$R_G=241\Omega$,	-	0.11	-	mJ
Turn-off energy	E_{off}	$L_{\sigma}^{(2)}=180\text{nH}$,	-	0.09	-	
Total switching energy	E_{ts}	$C_{\sigma}^{(2)}=40\text{pF}$ Energy losses include “tail” and diode ³⁾ reverse recovery.	-	0.2	-	

Anti-Parallel Diode Characteristic

Diode reverse recovery time	t_{rr}	$T_j=150^\circ\text{C}$ $V_R=800\text{V}$, $I_F=1\text{A}$, $R_G=241\Omega$	-	213	-	ns
Diode reverse recovery charge	Q_{rr}		-	180	-	μC
Diode peak reverse recovery current	I_{rrm}		-	2.7	-	A
Diode current slope	di_F/dt		-	240	-	A/ μs
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	135	-	

²⁾ Leakage inductance L_{σ} and stray capacity C_{σ} due to dynamic test circuit in figure E

³⁾ Commutation diode from device IKP01N120H2

Switching Energy ZVT, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-off energy	E_{off}	$V_{CC}=800V$, $I_C=1A$, $V_{GE}=15V/0V$, $R_G=241\Omega$, $C_r^{2)}=1nF$ $T_j=25^{\circ}C$ $T_j=150^{\circ}C$	- -	0.02 0.044	- -	mJ

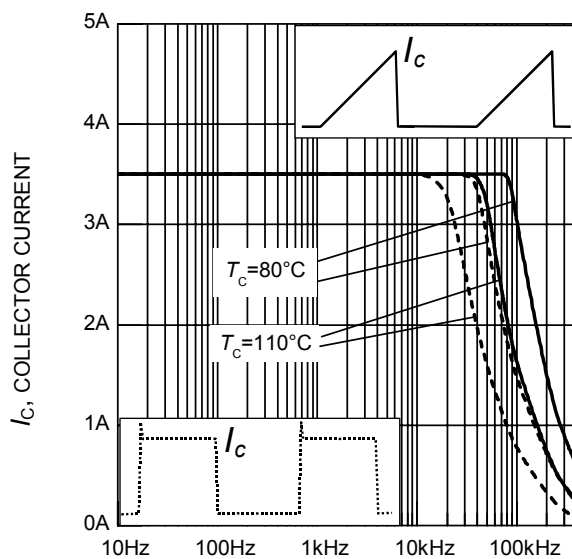

 f , SWITCHING FREQUENCY

Figure 1. Collector current as a function of switching frequency

($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $R_G = 241\Omega$)

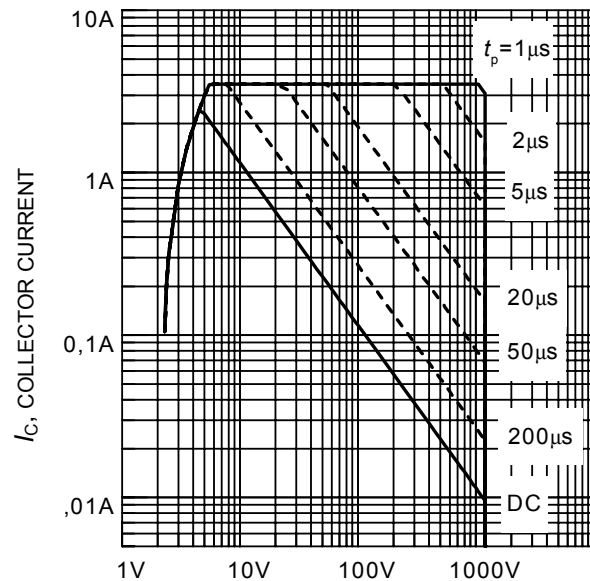

 V_{CE} , COLLECTOR-EMITTER VOLTAGE

Figure 2. Safe operating area
($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)

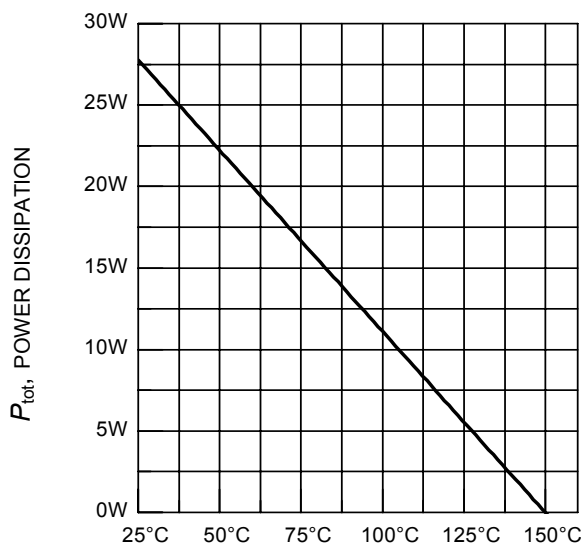

 T_C , CASE TEMPERATURE

Figure 3. Power dissipation as a function of case temperature

($T_j \leq 150^\circ\text{C}$)

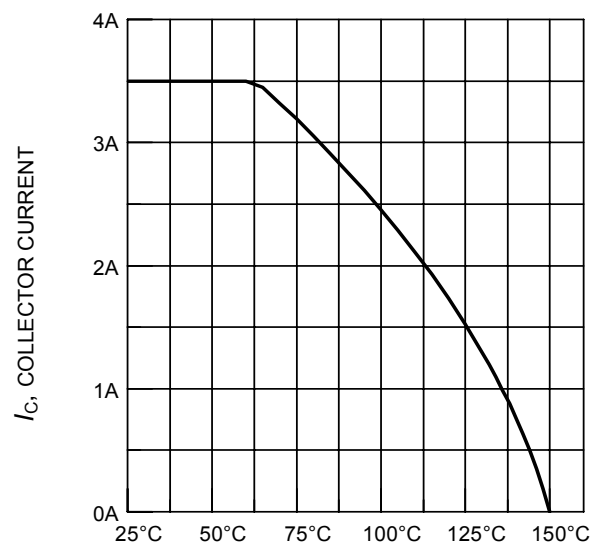

 T_C , CASE TEMPERATURE

Figure 4. Collector current as a function of case temperature

($V_{GE} \leq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

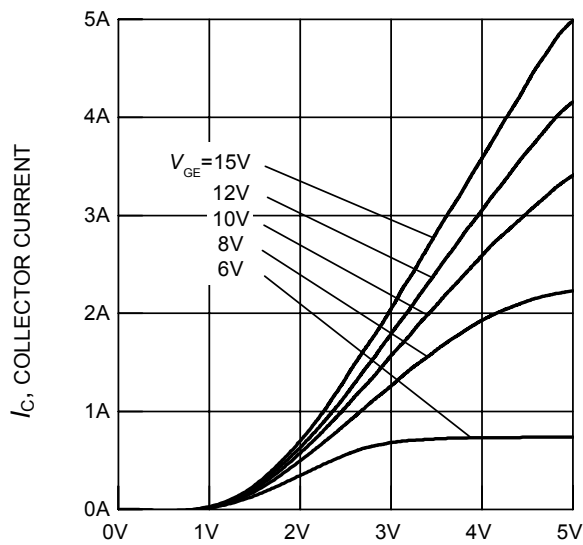

 V_{CE} , COLLECTOR-EMITTER VOLTAGE

Figure 5. Typical output characteristics
($T_j = 25^\circ\text{C}$)

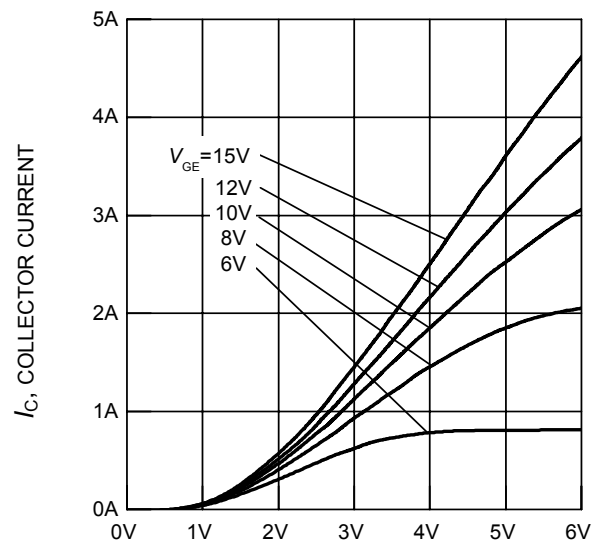

 V_{CE} , COLLECTOR-EMITTER VOLTAGE

Figure 6. Typical output characteristics
($T_j = 150^\circ\text{C}$)

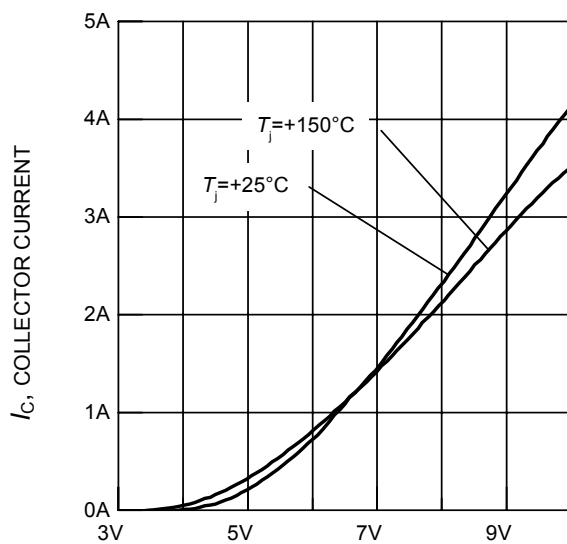

 V_{GE} , GATE-EMITTER VOLTAGE

Figure 7. Typical transfer characteristics
($V_{CE} = 20\text{V}$)

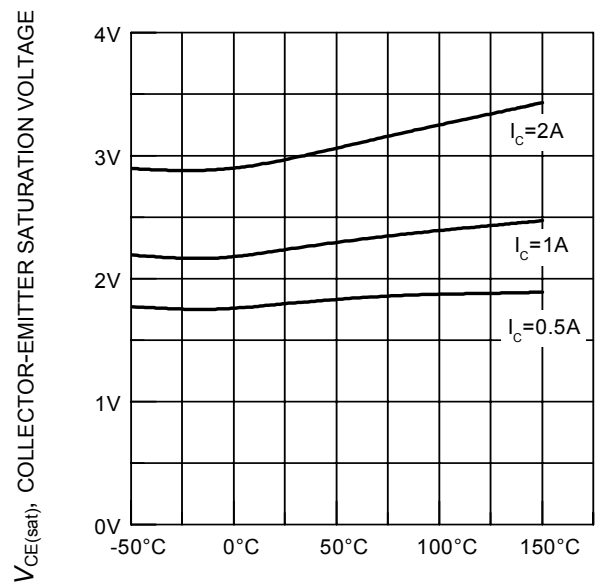

 T_j , JUNCTION TEMPERATURE

Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

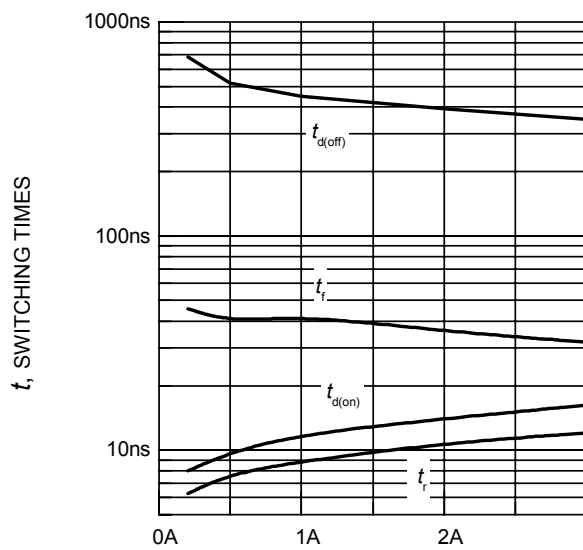

 I_C , COLLECTOR CURRENT

Figure 9. Typical switching times as a function of collector current

(inductive load, $T_j = 150^\circ\text{C}$,
 $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $R_G = 241\Omega$,
dynamic test circuit in Fig.E)

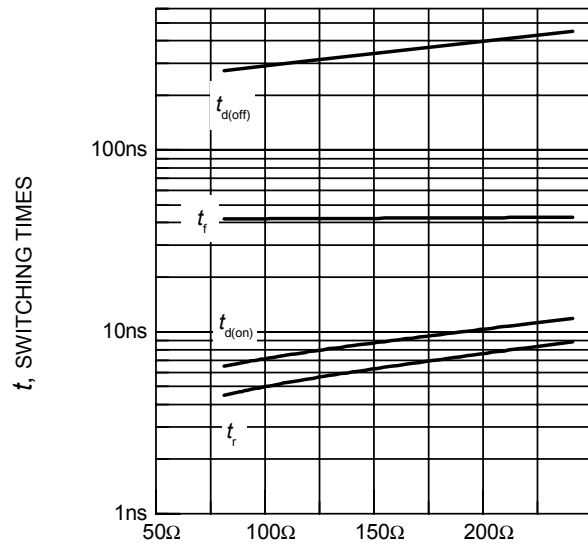

 R_G , GATE RESISTOR

Figure 10. Typical switching times as a function of gate resistor

(inductive load, $T_j = 150^\circ\text{C}$,
 $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 1\text{A}$,
dynamic test circuit in Fig.E)

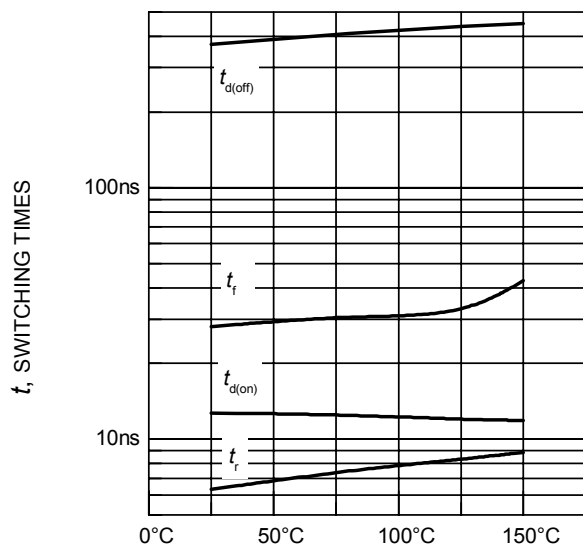

 T_j , JUNCTION TEMPERATURE

Figure 11. Typical switching times as a function of junction temperature

(inductive load, $V_{CE} = 800\text{V}$,
 $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 1\text{A}$, $R_G = 241\Omega$,
dynamic test circuit in Fig.E)

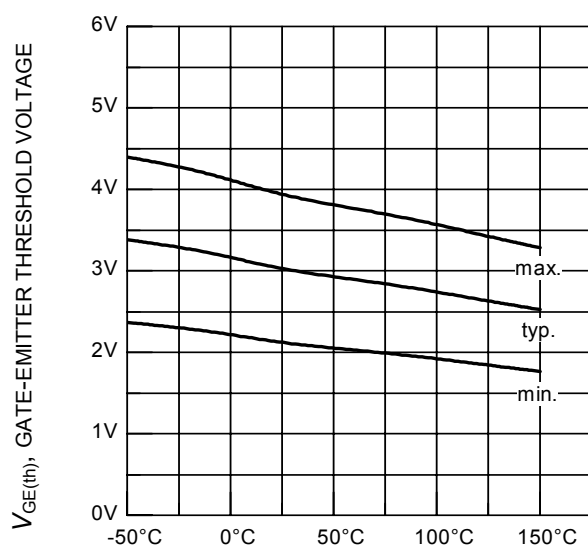

 T_j , JUNCTION TEMPERATURE

Figure 12. Gate-emitter threshold voltage as a function of junction temperature
($I_C = 0.03\text{mA}$)

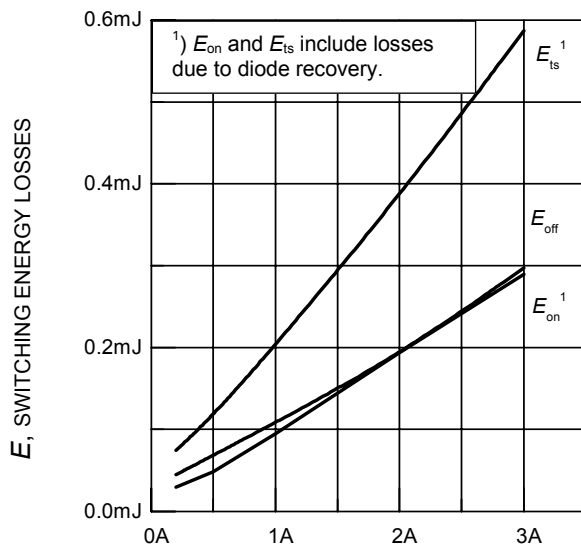

 I_C , COLLECTOR CURRENT

Figure 13. Typical switching energy losses as a function of collector current

(inductive load, $T_J = 150^\circ\text{C}$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $R_G = 241\Omega$, dynamic test circuit in Fig.E)

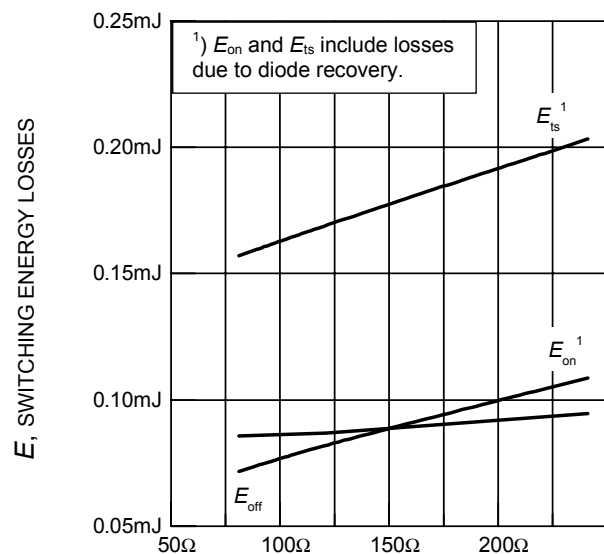

 R_G , GATE RESISTOR

Figure 14. Typical switching energy losses as a function of gate resistor

(inductive load, $T_J = 150^\circ\text{C}$, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 1\text{A}$, dynamic test circuit in Fig.E)

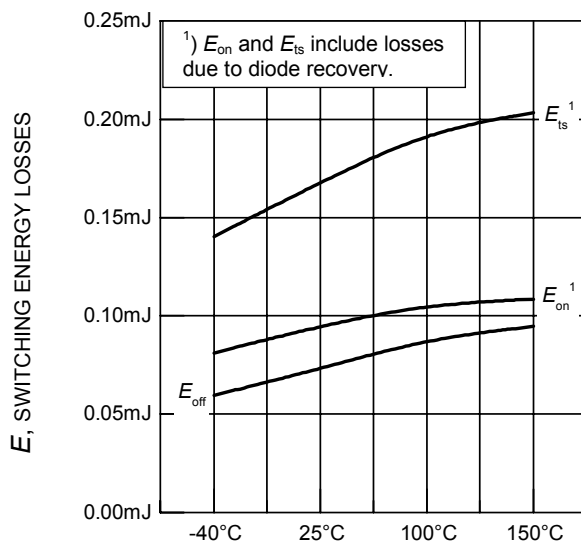

 T_J , JUNCTION TEMPERATURE

Figure 15. Typical switching energy losses as a function of junction temperature

(inductive load, $V_{CE} = 800\text{V}$, $V_{GE} = +15\text{V}/0\text{V}$, $I_C = 1\text{A}$, $R_G = 241\Omega$, dynamic test circuit in Fig.E)

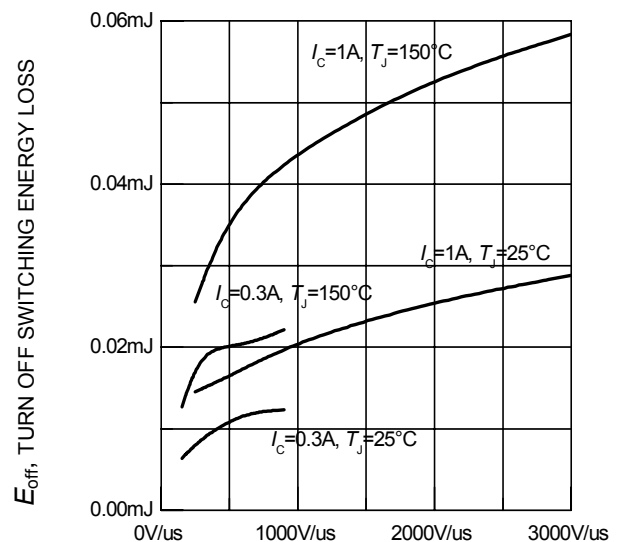

 dv/dt , VOLTAGE SLOPE

Figure 16. Typical turn off switching energy loss for soft switching
(dynamic test circuit in Fig. E)

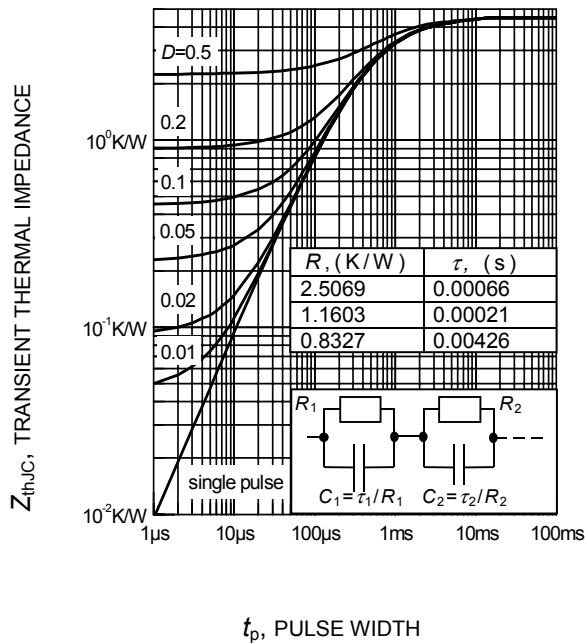


Figure 17. IGBT transient thermal impedance as a function of pulse width
($D = t_p / T$)

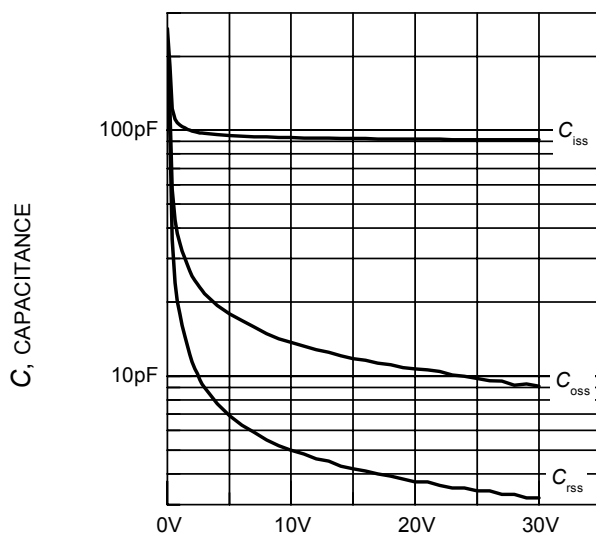


Figure 19. Typical capacitance as a function of collector-emitter voltage
($V_{GE} = 0V$, $f = 1MHz$)

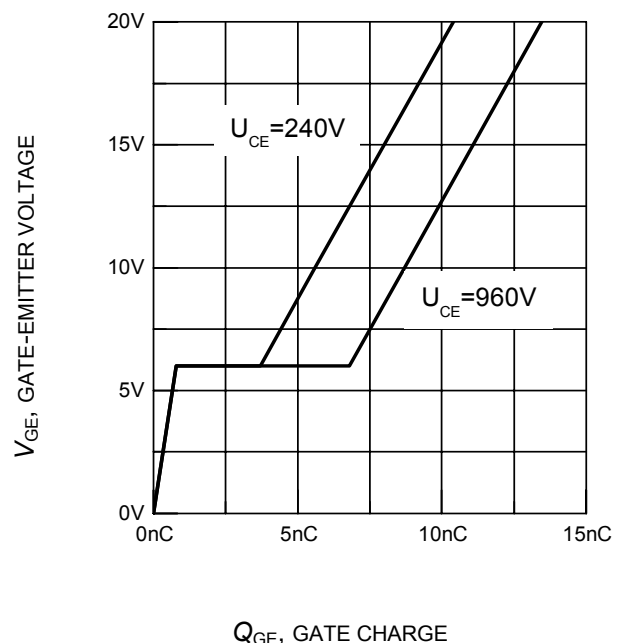


Figure 18. Typical gate charge
($I_C = 1A$)

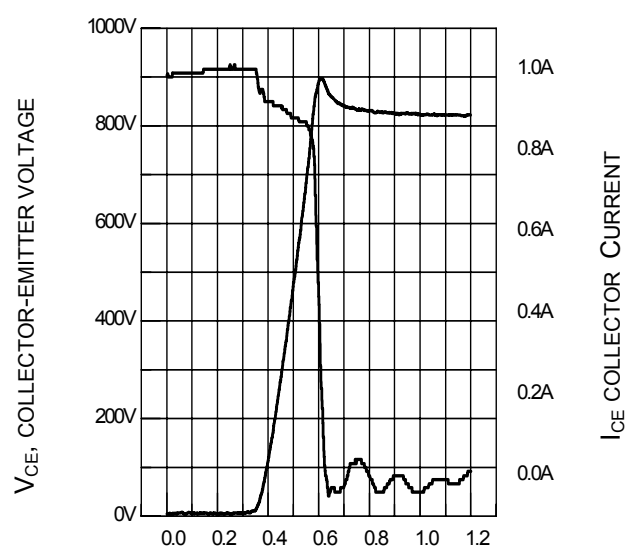


Figure 20. Typical turn off behavior, hard switching
($V_{GE} = 15/0V$, $R_G = 220\Omega$, $T_j = 150^\circ C$,
Dynamic test circuit in Figure E)

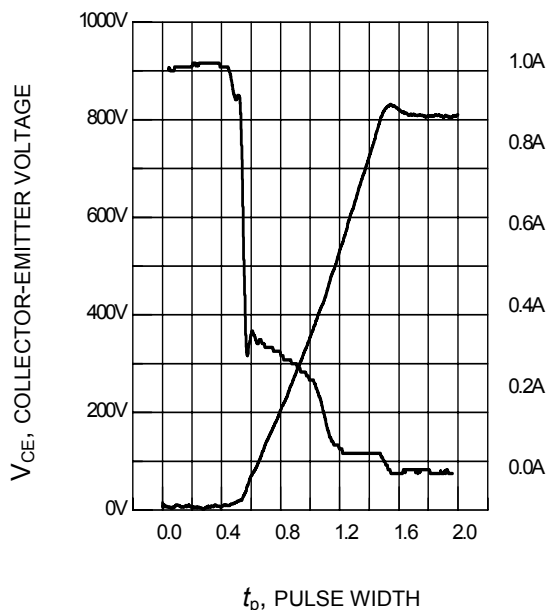


Figure 21. Typical turn off behavior, soft switching
($V_{GE}=15/0V$, $R_G=220\Omega$, $T_J = 150^\circ C$,
Dynamic test circuit in Figure E)

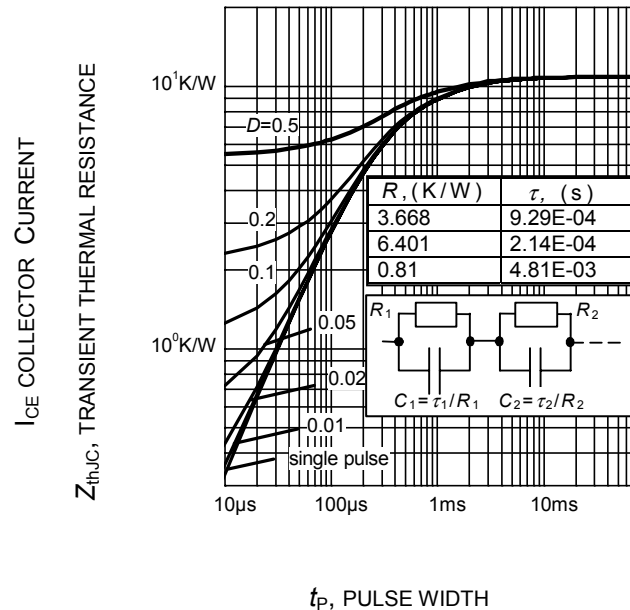


Figure 22. Diode transient thermal impedance as a function of pulse width
($D=t_p/T$)

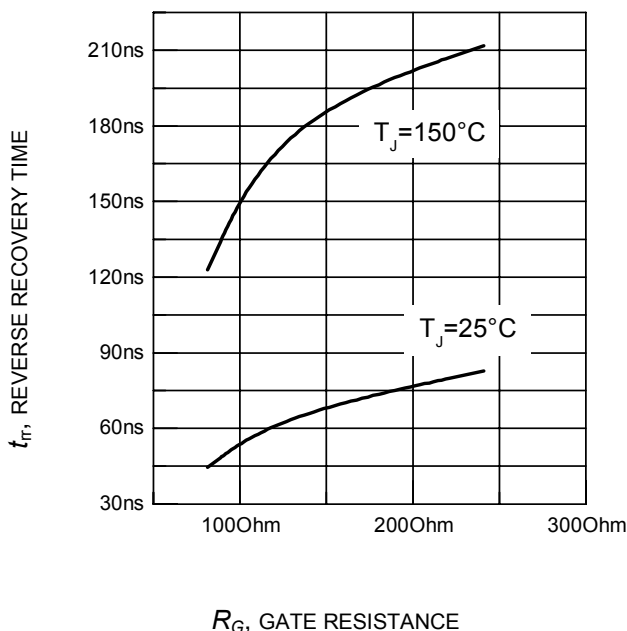


Figure 23. Typical reverse recovery time as a function of diode current slope
 $V_R=800V$, $I_F=3A$,
Dynamic test circuit in Figure E)

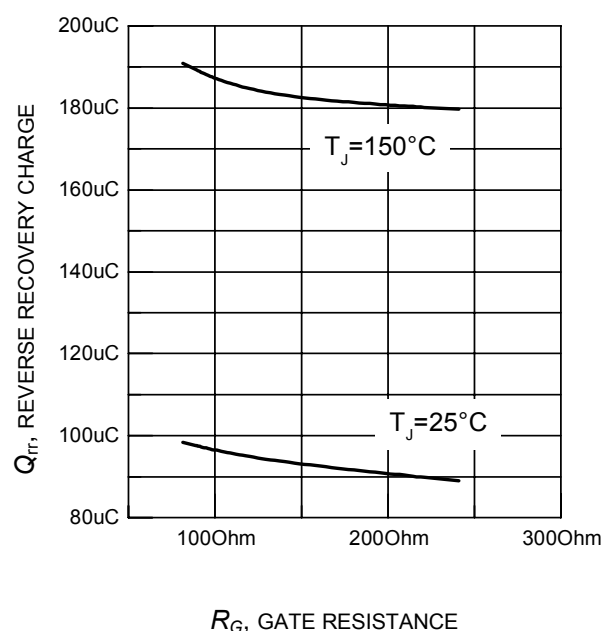


Figure 24. Typical reverse recovery charge as a function of diode current slope
($V_R=800V$, $I_F=3A$,
Dynamic test circuit in Figure E)

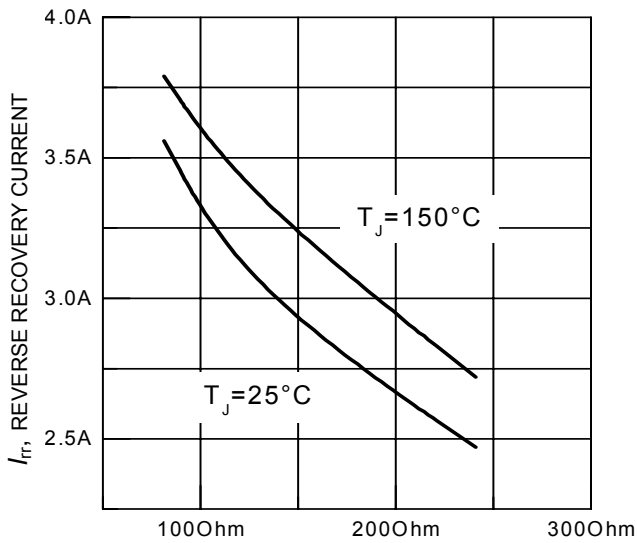

 R_G , GATE RESISTANCE

Figure 25. Typical reverse recovery current as a function of diode current slope
($V_R=800V$, $I_F=3A$,
Dynamic test circuit in Figure E)

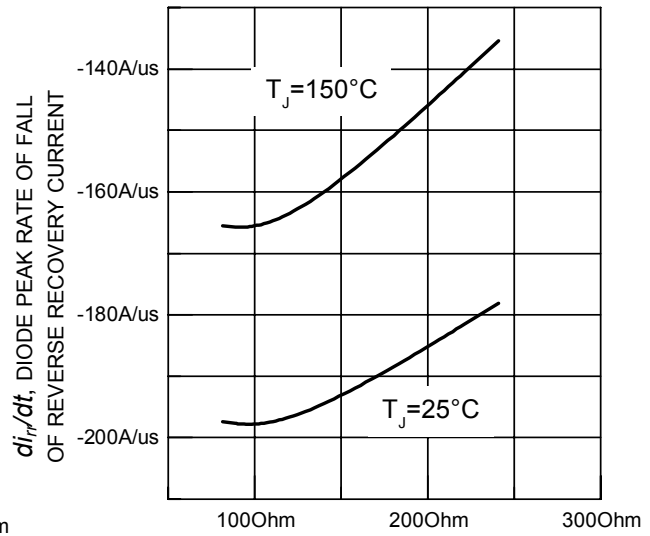

 R_G , GATE RESISTANCE

Figure 26. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
($V_R=800V$, $I_F=3A$,
Dynamic test circuit in Figure E)

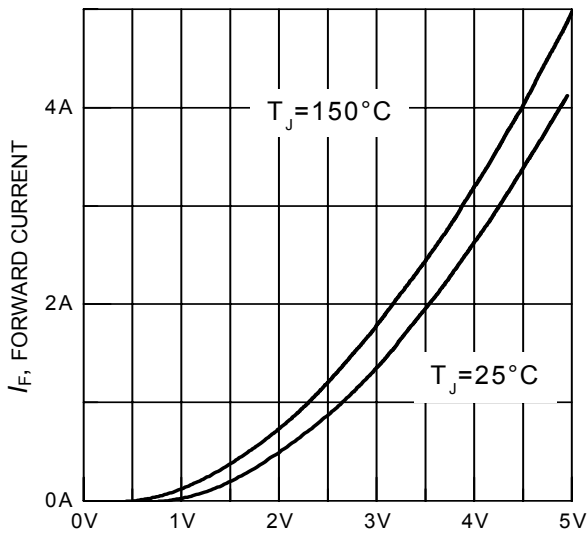

 V_F , FORWARD VOLTAGE

Figure 27. Typical diode forward current as a function of forward voltage

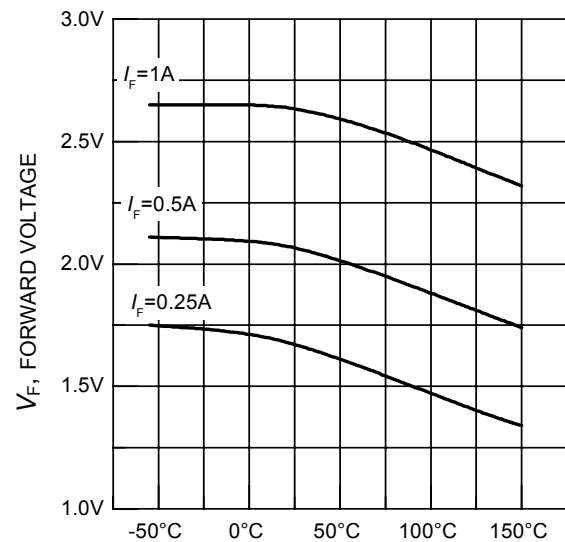
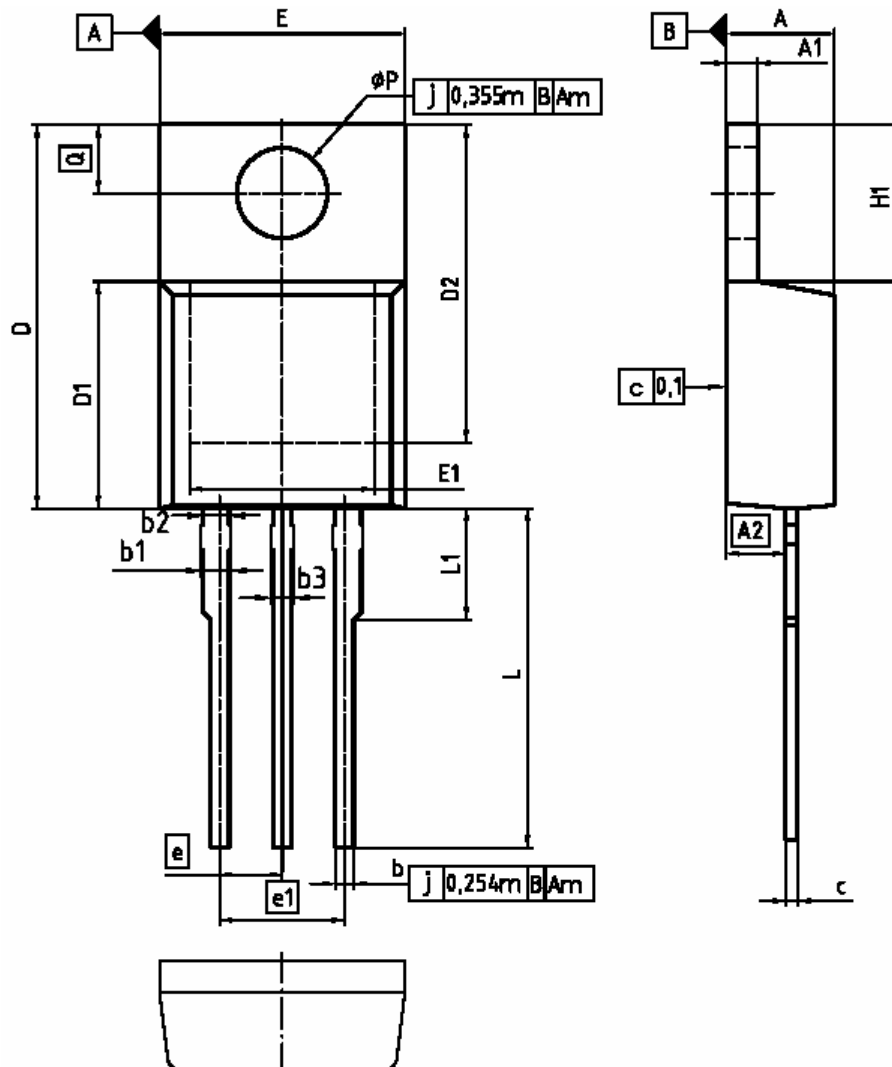
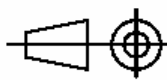

 T_J , JUNCTION TEMPERATURE

Figure 28. Typical diode forward voltage as a function of junction temperature

PG-TO220-3-1



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.67	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.65	1.15	0.026	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.80	0.013	0.031
D	14.81	15.95	0.583	0.628
D1	8.61	9.45	0.339	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.60	8.60	0.259	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
mP	3.80	3.89	0.142	0.153
q	2.80	3.00	0.102	0.118

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REVISION 05

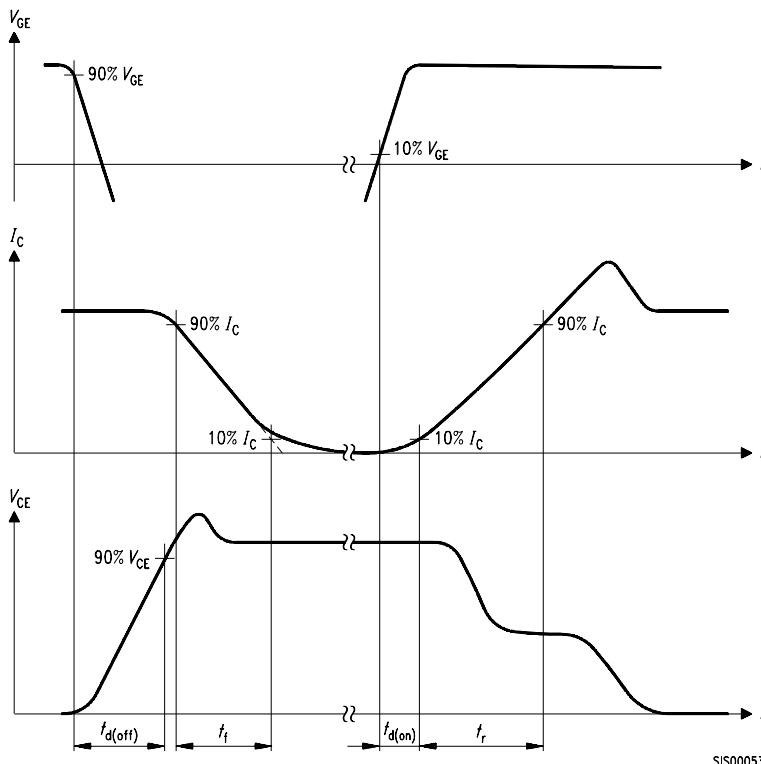


Figure A. Definition of switching times

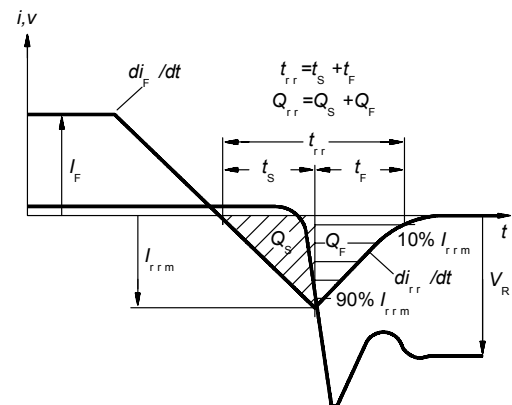


Figure C. Definition of diodes switching characteristics

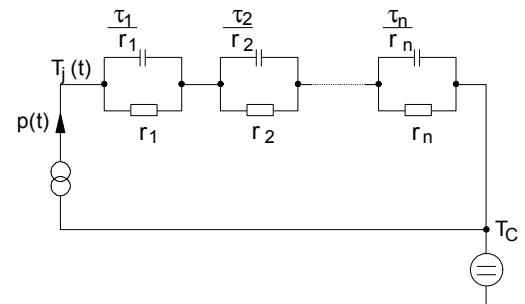


Figure D. Thermal equivalent circuit

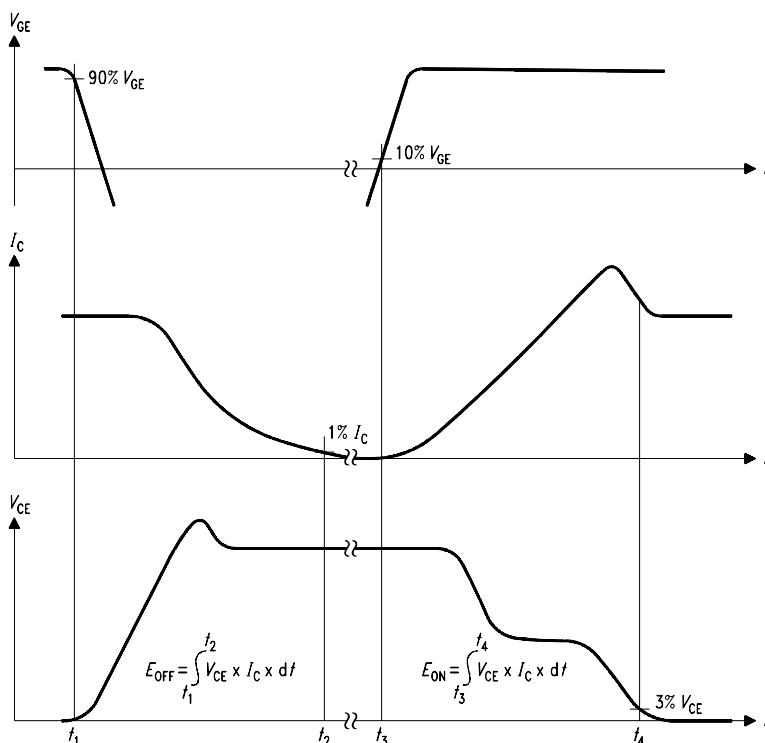


Figure B. Definition of switching losses

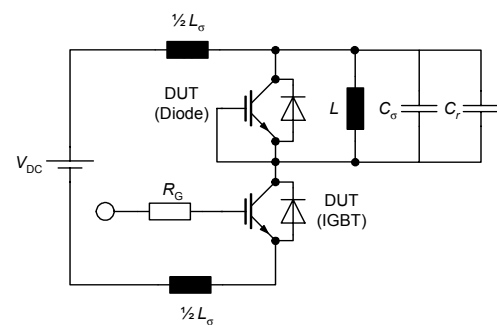


Figure E. Dynamic test circuit
Leakage inductance $L_\sigma = 180\text{nH}$,
Stray capacitor $C_\sigma = 40\text{pF}$,
Relief capacitor $C_r = 1\text{nF}$ (only for ZVT switching)

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